

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2467-Y

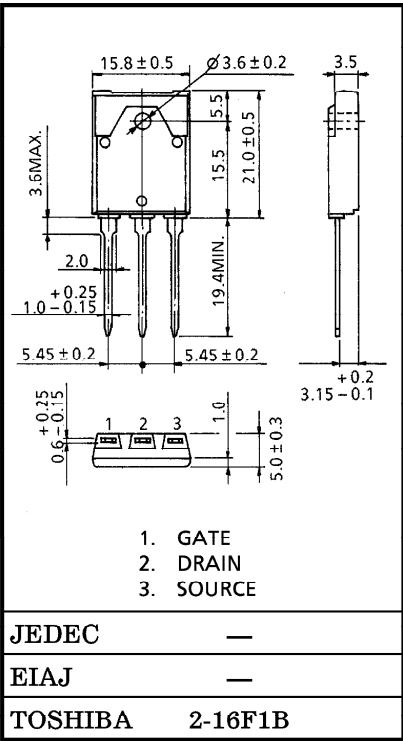
HIGH POWER AMPLIFIER APPLICATION

Unit in mm

- High Breakdown Voltage : $V_{DSS}=180V$
- High Forward Transfer Admittance : $|Y_{fs}|=4.0S$ (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	9	A
Drain Power Dissipation ($T_c=25^\circ C$)	P_D	80	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Weight : 5.8g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I_{DSS}	$V_{DS}=180V, V_{GS}=0$	—	—	1.0	mA
Gate Leakage Current	I_{GSS}	$V_{DS}=0, V_{GS}=\pm 20V$	—	—	± 0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR) DSS}$	$I_D=10mA, V_{GS}=0$	180	—	—	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$V_{GS}=10V, I_D=6A$	—	2.5	5.0	V
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	$V_{DS}=10V, I_D=0.1A$	1.4	—	2.8	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=3A$	—	4.0	—	S
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	700	—	pF
Output Capacitance	C_{oss}	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	150	—	pF
Reverse Capacitance	C_{rss}	$V_{DS}=30V, V_{GS}=0, f=1MHz$	—	90	—	pF

(Note) : $V_{GS(OFF)}$ Classification Y : 1.4~2.8

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

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